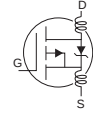


Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	-100	—	—	V	$V_{GS} = 0V$, $I_D = -250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	-0.11	—	V/ $^\circ\text{C}$	Reference to 25°C , $I_D = -1mA$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	0.20	Ω	$V_{GS} = -10V$, $I_D = -8.4A$ ④
$V_{GS(th)}$	Gate Threshold Voltage	-2.0	—	-4.0	V	$V_{DS} = V_{GS}$, $I_D = -250\mu A$
g_{fs}	Forward Transconductance	3.2	—	—	S	$V_{DS} = -50V$, $I_D = -8.4A$
I_{DSS}	Drain-to-Source Leakage Current	—	—	-25	μA	$V_{DS} = -100V$, $V_{GS} = 0V$
		—	—	-250		$V_{DS} = -80V$, $V_{GS} = 0V$, $T_J = 150^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 20V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -20V$
Q_g	Total Gate Charge	—	—	58	nC	$I_D = -8.4A$
Q_{gs}	Gate-to-Source Charge	—	—	8.3		$V_{DS} = -80V$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	—	32		$V_{GS} = -10V$, See Fig. 6 and 13 ④
$t_{d(on)}$	Turn-On Delay Time	—	15	—	ns	$V_{DD} = -50V$
t_r	Rise Time	—	58	—		$I_D = -8.4A$
$t_{d(off)}$	Turn-Off Delay Time	—	45	—		$R_G = 9.1\Omega$
t_f	Fall Time	—	46	—		$R_D = 6.2\Omega$, See Fig. 10 ④
L_D	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6mm (0.25in.) from package and center of die contact
L_S	Internal Source Inductance	—	7.5	—		
C_{iss}	Input Capacitance	—	760	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	260	—		$V_{DS} = -25V$
C_{rss}	Reverse Transfer Capacitance	—	170	—		$f = 1.0MHz$, See Fig. 5



Source-Drain Ratings and Characteristics

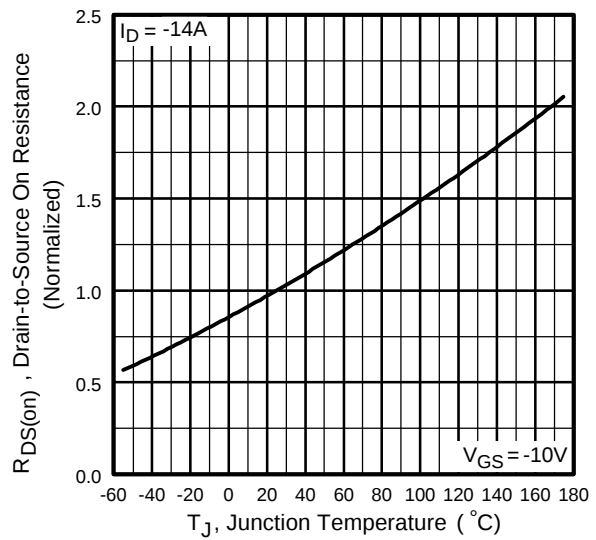
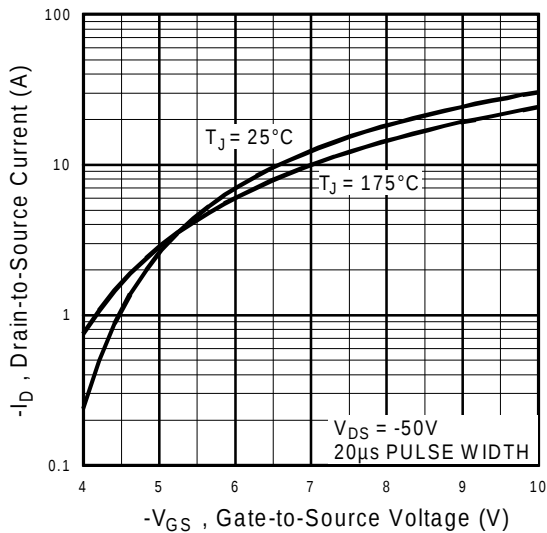
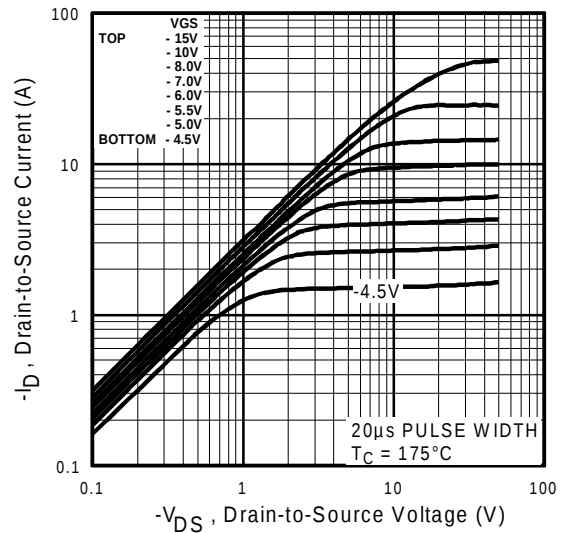
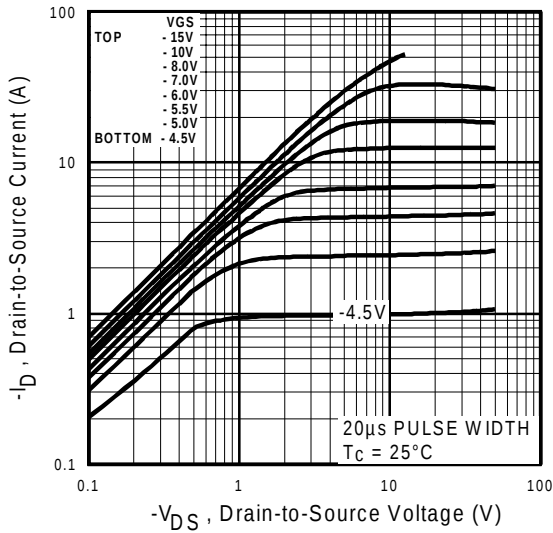
	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	-14	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	-56		
V_{SD}	Diode Forward Voltage	—	—	-1.6	V	$T_J = 25^\circ\text{C}$, $I_S = -8.4A$, $V_{GS} = 0V$ ④
t_{rr}	Reverse Recovery Time	—	130	190	ns	$T_J = 25^\circ\text{C}$, $I_F = -8.4A$
Q_{rr}	Reverse Recovery Charge	—	650	970	nC	$di/dt = -100A/\mu s$ ④
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S + L_D$)				

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)
- ② Starting $T_J = 25^\circ\text{C}$, $L = 7.0mH$
 $R_G = 25\Omega$, $I_{AS} = -8.4A$. (See Figure 12)

- ③ $I_{SD} \leq -8.4A$, $di/dt \leq -490A/\mu s$, $V_{DD} \leq V_{(BR)DSS}$,
 $T_J \leq 175^\circ\text{C}$

- ④ Pulse width $\leq 300\mu s$; duty cycle $\leq 2\%$.



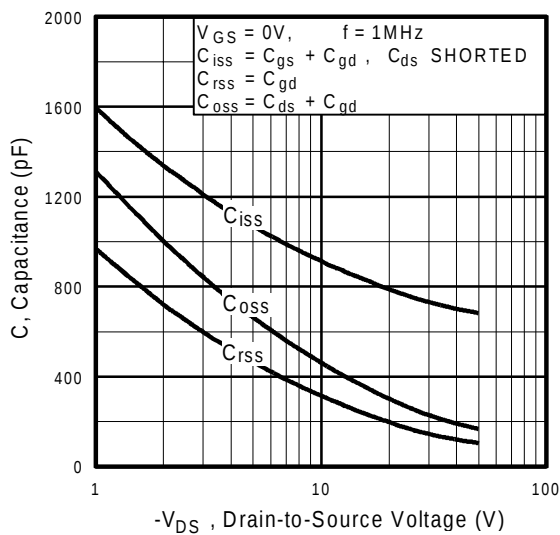


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

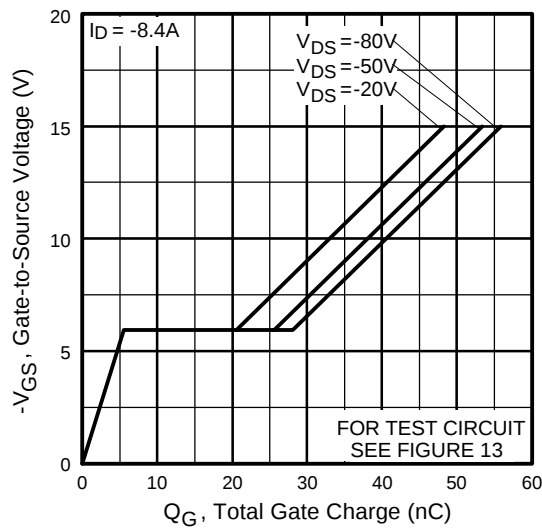


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

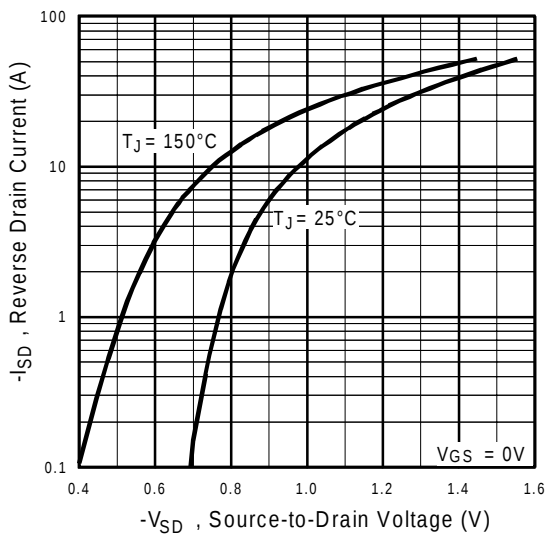


Fig 7. Typical Source-Drain Diode Forward Voltage

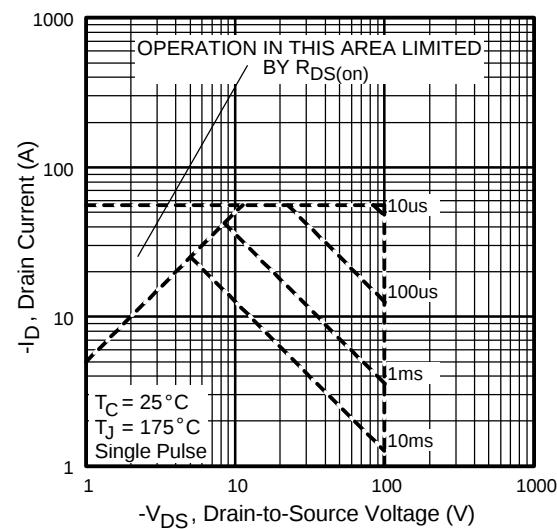


Fig 8. Maximum Safe Operating Area

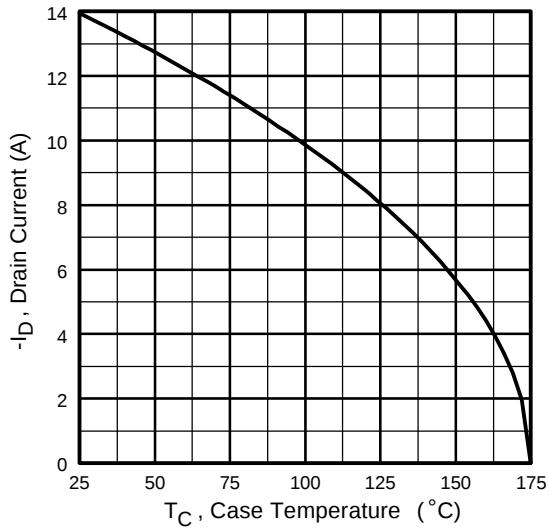


Fig 9. Maximum Drain Current Vs. Case Temperature

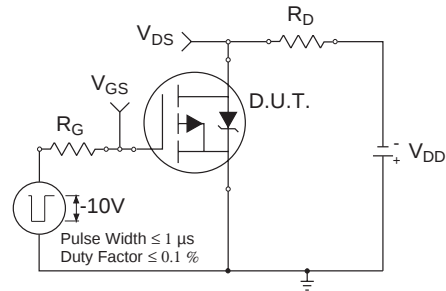


Fig 10a. Switching Time Test Circuit

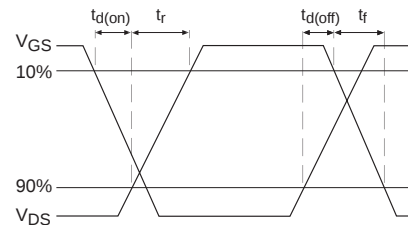


Fig 10b. Switching Time Waveforms

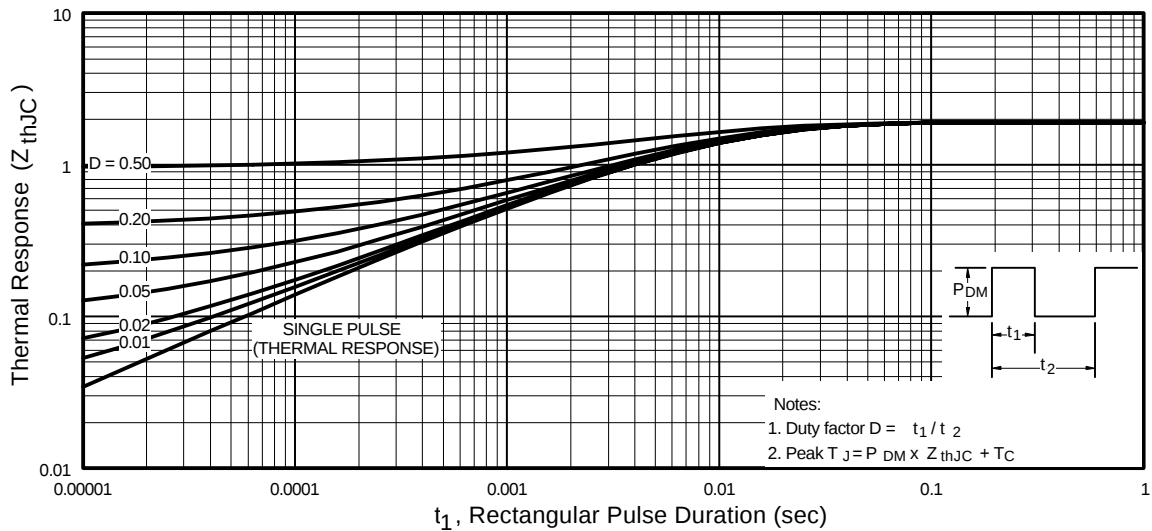


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

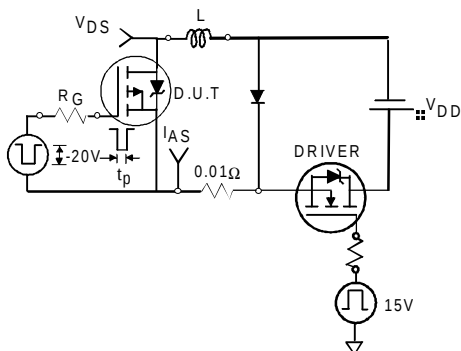


Fig 12a. Unclamped Inductive Test Circuit

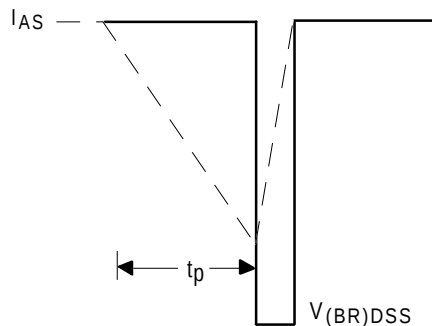


Fig 12b. Unclamped Inductive Waveforms

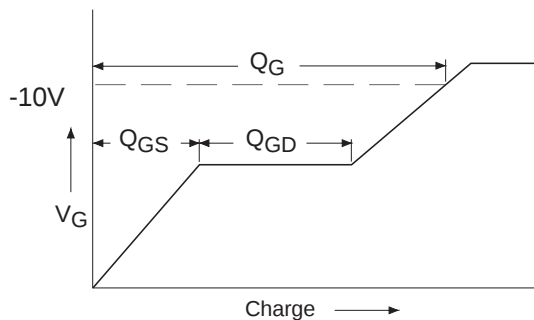


Fig 13a. Basic Gate Charge Waveform

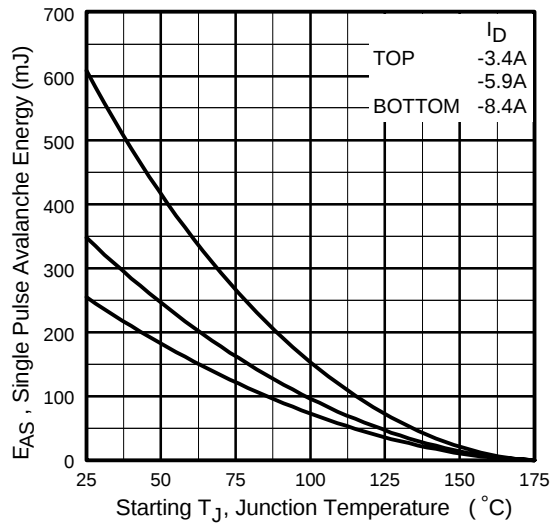


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

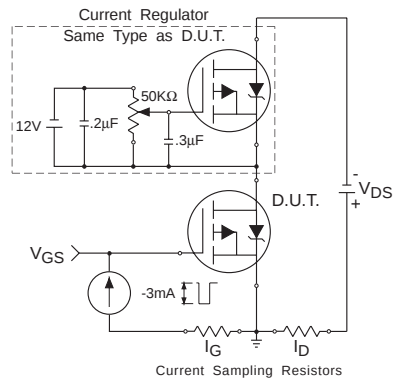
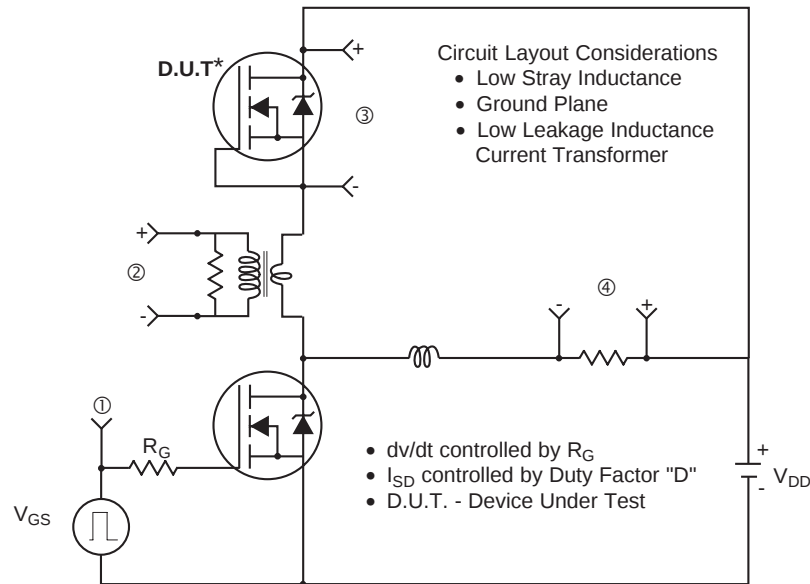
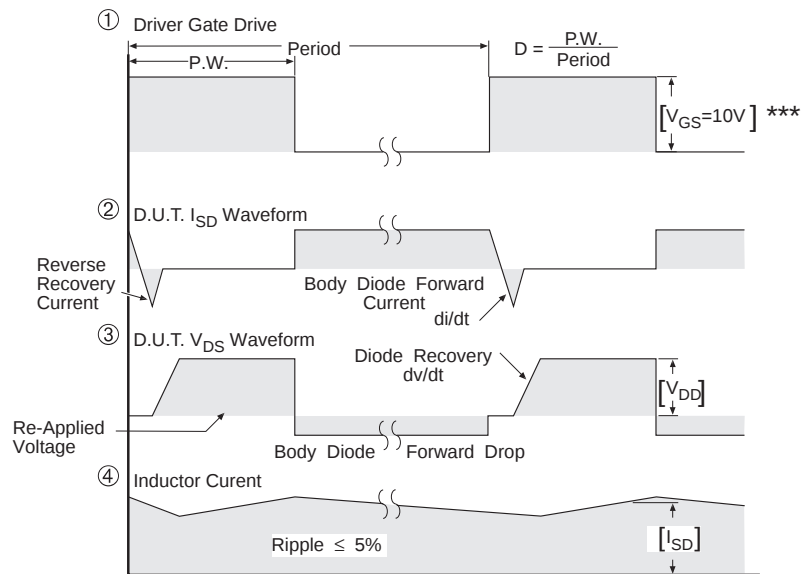


Fig 13b. Gate Charge Test Circuit

Peak Diode Recovery dv/dt Test Circuit



* Reverse Polarity of D.U.T for P-Channel



*** $V_{GS} = 5.0V$ for Logic Level and 3V Drive Devices

Fig 14. For P-Channel HEXFETS

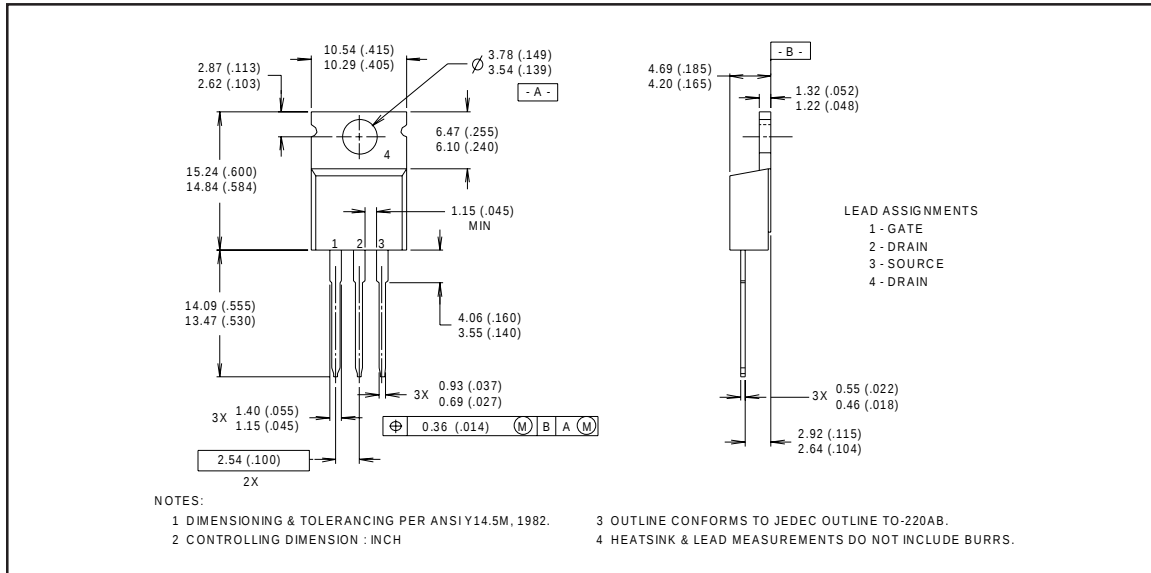
IRF9530N

International
IR Rectifier

Package Outline

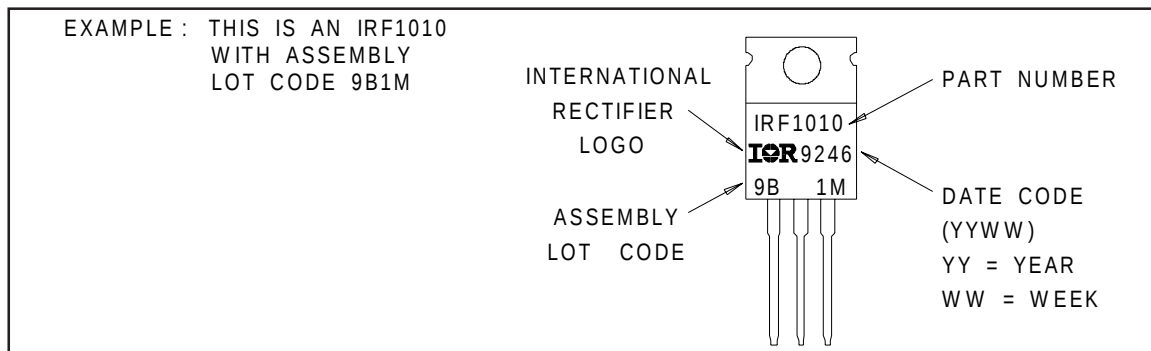
TO-220AB Outline

Dimensions are shown in millimeters (inches)



Part Marking Information

TO-220AB



International
IR Rectifier

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IR CANADA: 7321 Victoria Park Ave., Suite 201, Markham, Ontario L3R 2Z8, Tel: (905) 475 1897

IR GERMANY: Saalburgstrasse 157, 61350 Bad Homburg Tel: ++ 49 6172 96590

IR ITALY: Via Liguria 49, 10071 Borgaro, Torino Tel: ++ 39 11 451 0111

IR FAR EAST: K&H Bldg., 2F, 30-4 Nishi-Ikebukuro 3-Chome, Toshima-ku, Tokyo Japan 171 Tel: 81 3 3983 0086

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Note: For the most current drawings please refer to the IR website at:
<http://www.irf.com/package/>